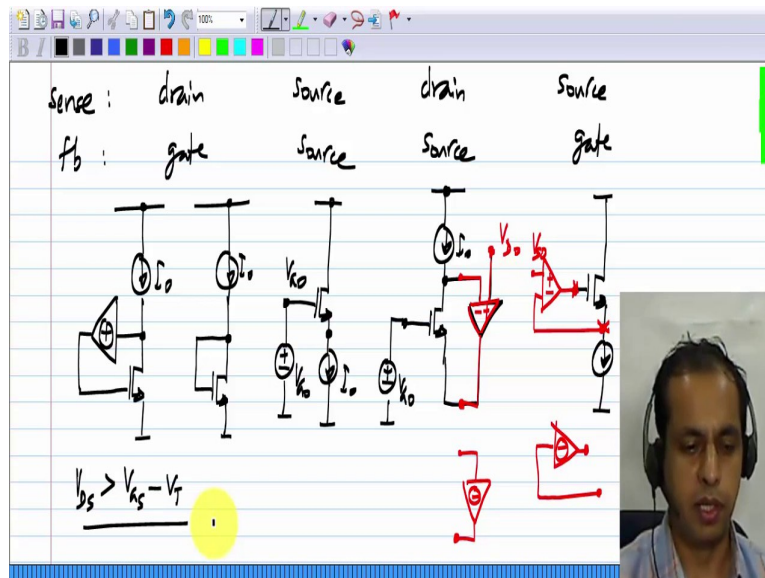


**Analog Circuits**  
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**Module - 04**

**Lecture – 10**

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We have discussed for varieties of biasing transistor at a given current  $I_0$ , and central to all these circuits is negative feedback. So, far our discussion has focused on the sense of negative feedback, when you use these things in an amplifier, you also want the transistor to be in saturation region; that means, that you have to get the sense of feedback correct as well as you have to get the bias voltages and so on correct so that the transistor remains in saturation. Now, we will discuss few of these issues. I will show all four types of setting a bias. The very first one was sensing at the drain and feeding back to the gate, the feedback to the gate has to be through a positive incremental gain, and you can do that.

Of course, the variant that we used because positive incremental gain also includes simply connecting it directly; by the way, I keep using the term gain here to describe this circuit positive incremental gain and so on. I do not really mean that it has to provide amplification that is the variation at the output does not have to be more than the input, it can work even if it is less. What I really mean is the sense of variation of output as the input is varied for this block. So, these two circuits are the same where this positive incremental gain is simply

replaced by the wire. And we also looked at sensing at the source and feeding back to the source where the gate is biased at a fixed voltage  $V_{G0}$ , so it really means that I have a voltage source  $V_{G0}$  or it is derived from a voltage divider and so on. I have  $I_0$  here, then we looked at sensing at the drain and feeding back to the source, where we connect the current source to the drain. The gate is biased at some  $V_{G0}$ , and an example was to use an op amp. In general, this part of it that I will show in red, this can be any circuit that has a negative incremental gain.

And lastly we sensed at the source and fed back to the gate, and the circuit looks like this. This is the example that we took and this I call  $V_{S0}$  so that means, that it is connected to a voltage source value of  $V_{S0}$  or it somehow biased at  $V_{S0}$ . And in general, circuitry from there to there, it can be any circuit with a negative incremental gain. So that is the idea. Now, after you do this, there are, of course, many realizations possible for this positive incremental gain or these negative incremental gains and choice of these bias voltages  $V_{D0}$ ,  $V_{S0}$  and so on. After that you have to check separately and ensure that the transistor is in saturation so; that means, that  $V_{DS}$  is more than  $V_{GS} - V_T$ . So, I will show it for a couple of examples and you can work it out yourself from assignment problems or activity problems and you can even create your own examples.

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Handwritten notes on a whiteboard defining the saturation region of a MOS transistor. The notes include a circuit diagram of a MOSFET with drain (D) and source (S) terminals, gate (G), and threshold voltage ( $V_T$ ). The drain-source voltage is labeled  $V_{DS}$  and the gate-source voltage is  $V_{GS}$ . Below the diagram, the conditions for the saturation region are written:  $V_{DS} > V_{GS} - V_T$  and  $V_{DS} > V_G - V_T$ . A second set of equations shows  $V_{DS} - V_{GS} > V_G - V_{GS} - V_T$ , which simplifies to  $V_{DS} - V_{GS} > -V_T$ , leading to  $V_{DS} > V_{GS} - V_T$ . A yellow highlight is under the final result  $V_{DS} > V_{GS} - V_T$ . A small video inset shows a person wearing a headset.

So, first of all, saturation region of a MOS transistor is defined by the drain source voltage  $V_{DS}$  being greater than  $V_{GS} - V_T$ . There are many other ways to put this, sometimes this is

convenient to use when you can calculate  $V_{DS}$  and  $V_{GS}$ . Now,  $V_{DS}$  can also be written as  $V_D - V_S$  where  $V_D$  and  $V_S$  are the drain voltage and the source voltage with respect to some ground. And similarly,  $V_{GS}$  can be written as  $V_G - V_S$  where  $V_G$  and  $V_S$  are gate and source voltages with respect to the same ground,  $-V_T$ . Clearly you see here that  $V_S$  cancels out and the same thing can be equivalently written as  $V_D$  being more than  $V_G - V_T$ .

What does it say? So instead of even computing  $V_{DS}$ , you can just compare the drain voltage with the gate voltage. What is this saying, the drain voltage has to be more than gate voltage minus  $V_T$ , and  $V_T$ , in general, can be negative or positive, although for the most often used variety of transistor it is positive. So, we will continue the discussion assuming that  $V_T$  is positive. So, what is this saying, the drain voltage can go below the gate voltage, but not by more than one  $V_T$ . So, one way to visualize the transistor going into the triode region is to imagine this separation between the drain and source in terms of voltage of course, the voltage separation between drain and source becoming too small. So, if you have the drain at the same voltage as the source,  $V_{DS}$  will be zero and you will be operating at the origin of the  $I_D, V_{DS}$  characteristic, it will be in deep triode region.

As this voltage, as this separation increases, it goes towards saturation region; and if this separation exceeds  $V_{GS} - V_T$ , it will be in saturation region. Another way to think about it is the drain voltage going below the gate voltage that itself is allowed, because  $V_T$  is positive, so  $V_D$  has to be greater than some voltage that is smaller than the gate voltage. In our example, we have been considering  $V_T$  of 1 V, so  $(V_G - 1 \text{ V})$ . So, if  $V_G$  is 3 V, this means that the drain voltage has to be more than 2 V, it can go below the gate voltage, but not by more than one threshold voltage. So that is another way to think about it. And if you rearrange these things, you can also see that  $V_{GD}$  has to be less than  $V_T$  that is another way to think about it. I mean it is just the rearrangement of the same relationship, the gate drain voltage has to be smaller than  $V_T$ .

All these are restatements of the same thing, but depending on the circuit configuration one of these three relationships is actually easier to use than the others. So, this is just an aside, because I am going to discuss this with respect to the circuits that we already have.

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$V_D = V_G$

$V_D = V_G + V_x$

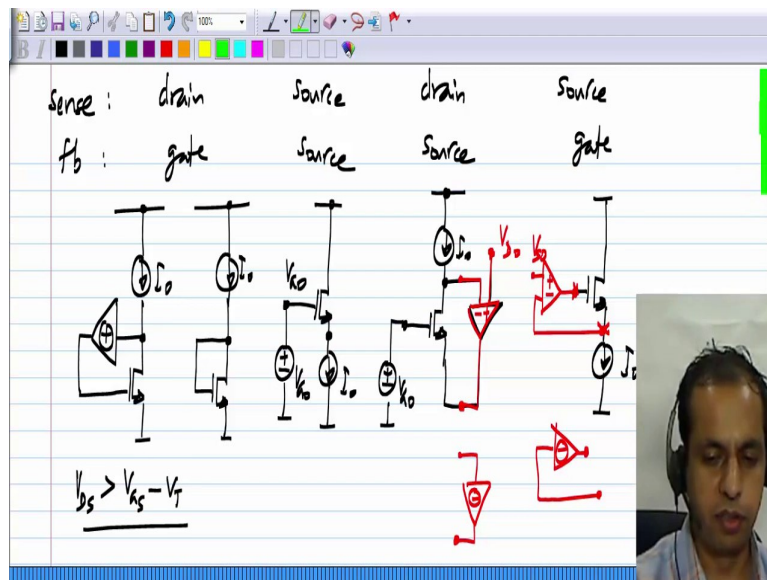
$V_D > V_G - V_T$

$V_x > -V_T$

The very first circuit sensing at the drain and feeding back to the gate, this is what we had. And we know the sense of feedback and the simplest variety was to just connect the drain to the gate, and this we know this will be in saturation region, because the threshold voltage is positive; that means, that  $V_D$  will be more than  $V_G - V_T$ , because in this case, after all,  $V_D$  equals  $V_G$ . So, this will be in saturation region. Now, another alternative which you would have seen in some activity questions or even discussed it in one of the earlier lessons is to have a voltage source. So, let us I call this  $V_x$  then now you see that  $V_D$  and  $V_G$  are not the same;  $V_D = V_G + V_x$ ; and  $V_D$  has to be greater than  $V_G - V_T$ . So, from these two, you can see that  $V_x$  has to be greater than  $-V_T$ .

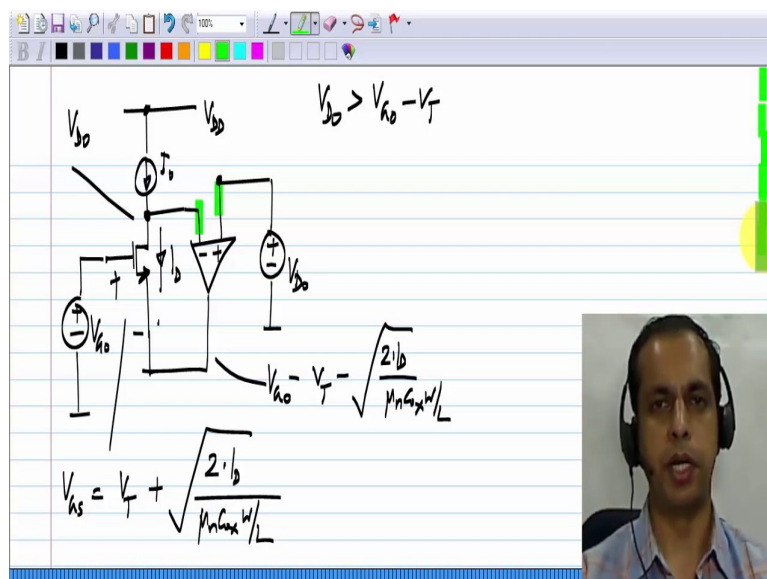
I have shown this with the positive polarity to the right towards the drain. Now, this  $V_x$  could be negative, but it cannot be more negative than one threshold voltage. If  $V_x$  is  $-0.5$  V, this will be in saturation region, but if it is  $-1.5$  V, this will go into triode region.

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So, that is as far as this particular circuit is concerned and this is true in every case because just for biasing for instance, in this case, nothing else is connected, in this case, nothing else is connected to the drain and so on. But when you turn this into some small signal incremental functionality, something will be connected to the drain; so you have to evaluate the saturation region separately that is what I am trying to say. The feedback has to be in the correct sense and the transistor has to be in the saturation for it to behave like a good amplifier.

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Let me consider an example where we sense at the drain and feedback to the source. We have the MOS transistor; to sense at the drain, we connect a current source  $I_0$ . And the drain current  $I_D$  is the current through the MOS transistor. We have the gate voltage  $V_{G0}$ , and the feedback loop is completed with some block which has a negative incremental gain. I will use an op amp with this polarity; we saw earlier that this maintains negative feedback around the transistor, as well as the op amp and that, is generally the case. And this point is connected to some fixed voltage, let me call that  $V_{D0}$ . So, now because of negative feedback around this, the current through the transistor will be  $I_0$ , and how does that happen by having the appropriate value of gate source voltage.

Now, assuming that the transistor is in saturation, the gate source voltage would be the threshold voltage plus square root of two times the drain current divided by the current factor. So, now the voltage at the source would be  $V_{G0}$  minus this voltage, -  $V_{GS}$ , which is

$$V_{GS} = V_T + \sqrt{2I_0 / \mu_n C_{ox} (W/L)}$$

. Now, the drain voltage here, what is that you can figure

out the value by realizing that the op amp inputs are virtually shorted, because the op amp is in negative feedback, so these two inputs are at the same voltage, so the drain voltage is  $V_{D0}$ . Now, how do you verify whether the transistor is in saturation region? By comparing the drain voltage to the gate voltage or drain source voltage to gate source voltage.

In this case, it is easier to compare drain voltage to the gate voltage, we know that  $V_{D0}$  has to be greater than  $(V_{G0} - V_T)$  for the transistor to be in saturation region. So, What decides whether the transistor is in saturation in this particular circuit are the values of  $V_{D0}$  and  $V_{G0}$ . And you have to choose them appropriately so that the transistor is maintained in saturation. And of course, there are circuits where you may want the transistor to be in triode region, again you have to choose the values of these things appropriately so that the transistor remains in triode region.

So, in summary, when you bias a transistor at a constant current, you are establishing a negative feedback loop, we know how to make the loop to have negative feedback that is eventually the circuit should settle to a point where the drain current is exactly equal to the desired current. If the drain current is more than desired current, somehow the gate source

voltage must reduce; and if the drain current is less than the desired current, the gate source voltage must increase. So, negative feedback ensures that, but of course, negative feedback only tells you in which direction to vary things. The absolute values of voltages are also important to maintain the transistor in saturation region. And you have to pick that appropriately. The negative feedback loop can be completed by a variety of means; in each case, you have to separately check and make sure that the transistor is in saturation.